

**AMENDMENTS TO THE SPECIFICATION**

1. Please substitute the paragraph [0009] on page 4 with the following amended paragraph:

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It is therefore a primary objective of the claimed invention to provide a method of fabricating a polysilicon film by an excimer laser crystallization ~~process~~which process which comprises a step of forming  
10 a heat-retaining capping layer so as to increase the grain size of the polysilicon film and improve the performance of devices.

2. Please substitute the paragraph [0010] on page 4 with the following amended paragraph:

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In a preferred embodiment, the claimed invention provides a method of fabricating a polysilicon film by an excimer laser crystallization process. First,  
20 a substrate comprising a first region and a second region is provided. An amorphous silicon layer and a mask layer are formed on the substrate in sequence. Then, a photo-etching process is performed to remove the mask layer in the first region. A heat-retaining  
25 capping layer is formed on the mask layer and the amorphous silicon layer. After that, an excimer laser ~~crystallization process~~ crystallization process is performed so that the amorphous silicon layer in the first region is crystallized into a polysilicon film.

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